

[WeA1] Gallium Oxides

Session Date	July 15 (Wed.), 2026
Session Time	10:25–12:10
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Dongwan Kim (Korea Research Institute of Standards and Science, Korea), Prof. Seokho Moon (Ajou University, Korea)

[WeA1–1] [Invited]

10:25–10:55

Atomic-Scale Interface and Polarity Engineering in III-Nitride and β -Ga₂O₃ Heterostructures by Hot-Wall MOVPE

Minho Kim¹, Alexis Papamichail², Ingmar Persson³, Hengfang Zhang¹, Dat Q. Tran¹, Ken Goto², Andri Dhora², Daniela Gogova¹, Per O. Å. Persson¹, Plamen P. Paskov¹ and Vanya Darakchieva^{1,2},
¹Linköping University, Sweden, ²Lund University, Sweden

[WeA1–2]

10:55–11:10

Effects and Applications of Nuclear Radiation in Ga₂O₃

Yoonho Choi, Jaeheon Jung, Hae Seong Hwang, and Roy B.Chung, Kyungpook National University, Korea

[WeA1–3]

11:10–11:25

AlN Mesa Sidewall Passivation Enables Thermally Stable Reverse Blocking in Vertical β -Ga₂O₃ Power Diodes

Ganesh Mainali, Nuzhat Yousf, Dhanu Chettri, Haicheng Cao, Leo Raj Solay, and Xiaohang Li, King, Abdullah University of Science and Technology, Kingdom of Saudi Arabia

[WeA1–4]

11:25–11:40

High Efficiency Growth of (001) β -Ga₂O₃ Films by Cold-Wall MOCVD

Shun Ukita and Hironori Okumura, University of Tsukuba, Japan

[WeA1-5]

11:40-11:55

Heteroepitaxial Growth of β -Ga₂O₃ on High-Angle Off-Cut Sapphire via MOCVD

Ji-Hyeon Park, Hyeong-Yun Kim, JungHun Choi, and Dae-Woo Jeon, Korea Institute of Ceramic Engineering and Technology, Korea

[WeA1-6]

11:55-12:10

Influence of Substrate Atomic Symmetry on the Epitaxy and Rotational Domain Formation of κ -Ga₂O₃

Ha Young Kang, Jaeheon Jung, Young Soo Hwang, and Roy B. Chung, Kyungpook National University, Korea